



COMPLEMENTRY SILICON DARLINGTON POWER TRANSISTORS



TO-66

NPN PNP 2N6300 2N6298 2N6301 2N6299

TO-66 Leaded Plastic Package RoHS compliant

GENERAL DISCRIPTION:

The 2N6298 ~ 2N6301 series types transistors are complementary silicon darlington power transistors manufactured by the epitaxial base process designed for high gain amplifier and medium speed switching applications.

FEATURES:

1. This product is available in AEC-Q101 Compliant and PPAP Capable also.

Note: For AEC-Q101 compliant products, please use suffix -AQ in the part number while ordering.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C Unless otherwise specified)

PARAMETERS	SYMBOL	2N6298 2N6300	2N6299 2N6301	UNIT
Collector-Base Voltage	V_{CBO}	60	80	V
Collector-Emitter Voltage	V_{CEO}	60	80	V
Emitter- Base Voltage	V_{EBO}	5.0		V
Collector Current	I _C	8.0		Α
Collector Current - Peak	I _{CM}	16.0		Α
Base Current	I _B	120		mA
Power Dissipation	P_{D}	75		W
Operating and Storage Junction Temperature	T_J, T_stg	-65 to +200		°C
Themal Resistance	$R_{ hetaj-c}$	2.33		°C/W







An IATF 16949, ISO9001 and ISO 14001/ISO 45001 Certified Company

ELECTRICAL CHARACTERISTICS at (Ta = 25 °C Unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	2N6298 2N6300		2N6299 2N6301		UNIT
			MIN	MAX	MIN	MAX	
Collector cut-off current	I _{CEV}	V_{CE} = Rated V_{CBO} , $V_{EB(off)}$ = 1.5v		0.5	-	0.5	mA
Collector cut-off current	I _{CEV}	V _{CE} =Rated V _{CBO} , V _{EB(off)} =1.5v, T _C =150°C		5.0	I	5.0	mA
Collector cut-off current	I _{CEO}	V _{CE} = ½ Rated V _{CEO}		0.5		0.5	mA
Emitter cut-off current	I _{EBO}	V _{BE} =5.0V		2.0		2.0	mA
Breakdown Voltage	BV _{CEO}	I _C =100mA	60		80		V
Collector – Emitter Saturation Voltage	$V_{CE(SAT)}$	I _C =4A, I _B =16mA		2.0		2.0	V
Collector – Emitter Saturation Voltage		$I_{\rm C}$ = 8A, $I_{\rm B}$ =80mA		3.0		3.0	V
Base – Emitter Saturation Voltage	$V_{BE(SAT)}$	$V_{CE} = 8V, I_{C} = 80mA$		4.0		4.0	V
Base – Emitter On Voltage	$V_{BE(ON)}$	$V_{CE} = 3.0V, I_{C} = 4A$		2.8		2.8	V
DC Current Gain	h _{FE}	V_{CE} =3.0V, I_{C} =4A	750	18K	750	18K	
DC Current Gain	h _{FE}	V_{CE} =3.0V, I_{C} =8.0A	100		100		
Small – Signal Current Gain	h _{fe}	V_{CE} =3.0V, I_{C} =3A, f = 1.0kHz	300		300		
Current – Gain Bandwidth Product	f _T	V_{CE} =3V, I_{C} =3A, f = 1.0 MHz	4.0		4.0		MHz
Capacitance between collector and base		V _{CB} =10V, IE = 0, f = 0.1MHz (NPN Type)		200	1	200	pF
	C_{ob}	V _{CB} =10V, IE = 0, f = 0.1MHz (PNP Type)		300		300	pF

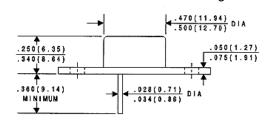


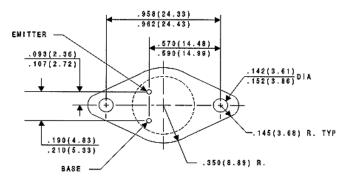




PACKAGE DETAILS

TO-66 Leaded Plastic Package





All Dimensions in Inches mm







Recommended Reflow Solder Profiles

The recommended reflow solder profiles for Pb and Pb-free devices are shown below.

Figure 1 shows the recommended solder profile for devices that have Pb-free terminal plating, and where a Pb-free solder is used.

Figure 2 shows the recommended solder profile for devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with a leaded solder.

Figure 1

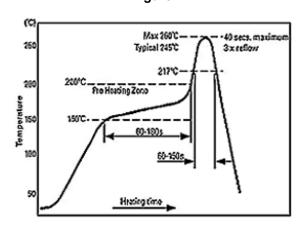
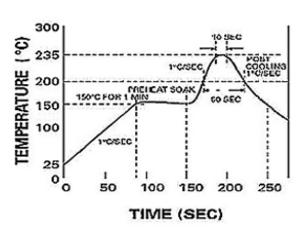


Figure 2



Reflow profiles in tabular form

Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~3°C/second	~3°C/second
Preheat – Temperature Range – Time	150-170°C 60-180 seconds	150-200°C 60-180 seconds
Time maintained above: – Temperature – Time	200°C 30-50 seconds	217°C 60-150 seconds
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	40 seconds
Ramp-Down Rate	3°C/second max.	6°C/second max.

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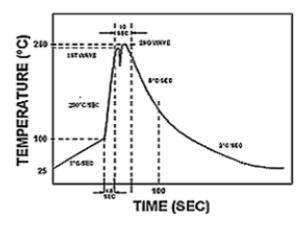




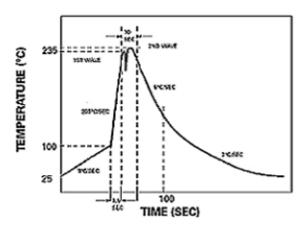


Recommended Wave Solder Profiles

The Recommended solder Profile For Devices with Pb-free terminal plating where a Pb-free solder is used



The Recommended solder Profile For Devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with leaded solder



Wave Profiles in Tabular Form

Profile Feature	Sn-Pb System	Pb-Free System	
Average Ramp-Up Rate	~200°C/second	~200°C/second	
Heating rate during preheat	Typical 1-2, Max 4°C/sec	Typical 1-2, Max 4°C/Sec	
Final preheat Temperature	Within 125°C of Solder Temp	Within 125°C of Solder Temp	
Peak Temperature	235°C	260°C max.	
Time within +0 -5°C of actual Peak	10 seconds	10 seconds	
Ramp-Down Rate	5°C/second max.	5°C/second max	







Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- · Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- · Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- · Mechanical stress such as vibration and impact shall be avoided.
- · The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level				
Level	Time	Condition		
1	Unlimited	≤30 °C / 85%		
2	1 Year	≤30 °C / 60%		
2a	4 Weeks	≤30 °C / 60%		
3	168 Hours	≤30 °C / 60%		
4	72 Hours	≤30 °C / 60%		
5	48 Hours	≤30 °C / 60%		
5a	24 Hours	≤30 °C / 60%		
6	Time on Label(TOL)	≤30 °C / 60%		

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Customer Notes

Component Disposal Instructions

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



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